

● General Description

The AGM205D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

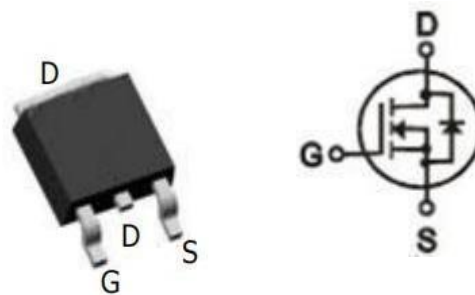
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
20V	2.8mΩ	90A

TO-252 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM205D	AGM205D	TO-252	330mm	16mm	2500

Table 1. Absolute Maximum Ratings (TC=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	20	V
VGS	Gate-Source Voltage (VDS=0V)	±12	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	90	A
	Drain Current-Continuous(Tc=100°C)	59	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	360	A
PD	Maximum Power Dissipation(Tc=25°C)	68	w
	Maximum Power Dissipation(Tc=100°C)	27	w
EAS	Avalanche energy (Note 3)	340	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	--	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	1.85	°C/W

Table 3. Electrical Characteristics (TC=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	20	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=20V,VGS=0V	--	--	1.0	μA
IGSS	Gate-Body Leakage Current	VGS=±12V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	0.4	0.7	1.1	V
RDS(on)	Drain-Source On-State Resistance	VGS=4.5V, ID=30A	--	2.8	4.0	mΩ
		VGS=2.5V, ID=20A	--	4.0	6.0	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=15V,VGS=0V, F=1MHZ	--	3200	--	pF
Coss	Output Capacitance		--	460	--	pF
Crss	Reverse Transfer Capacitance		--	445	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	1.1	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=4.5V,VDS=15V RG=17A,RGEN=1.8Ω	--	9.7	--	nS
tr	Turn-on Rise Time		--	37	--	nS
td(off)	Turn-Off Delay Time		--	63	--	nS
tf	Turn-Off Fall Time		--	52	--	nS
Qg	Total Gate Charge	VGS=4.5V, VDS=15V, ID=17A	--	48	--	nC
Qgs	Gate-Source Charge		--	3.6	--	nC
Qgd	Gate-Drain Charge		--	19	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	90	A
VSD	Forward on Voltage	VGS=0V,IS=30A	--	--	1.2	V
trr	Reverse Recovery Time	IF=30A , dI/dt=100A/μs ,	--	23	--	ns
Qrr	Reverse Recovery Charge	TJ=25°C	--	10	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

N- Channel Typical Characteristics

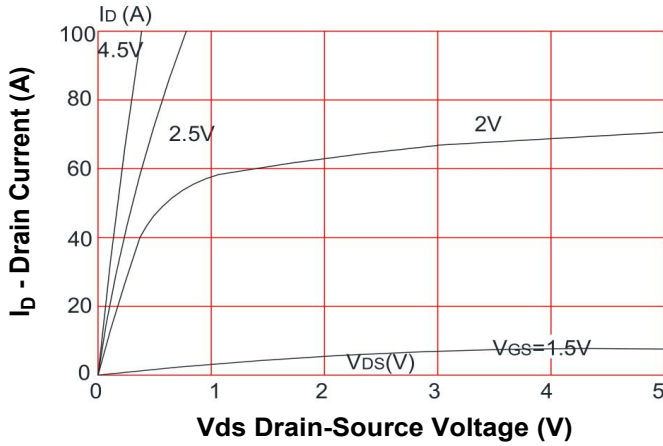


Figure 1. On-Region Characteristics

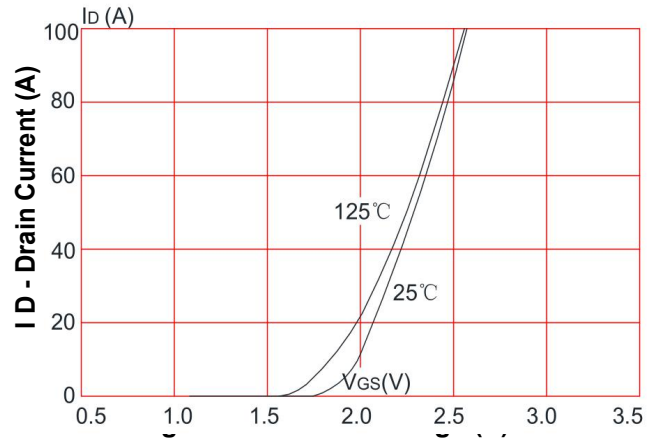


Figure 2. Transfer Characteristics

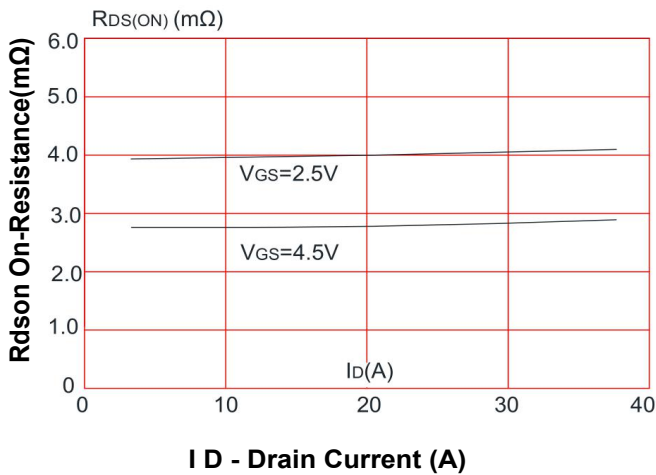


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

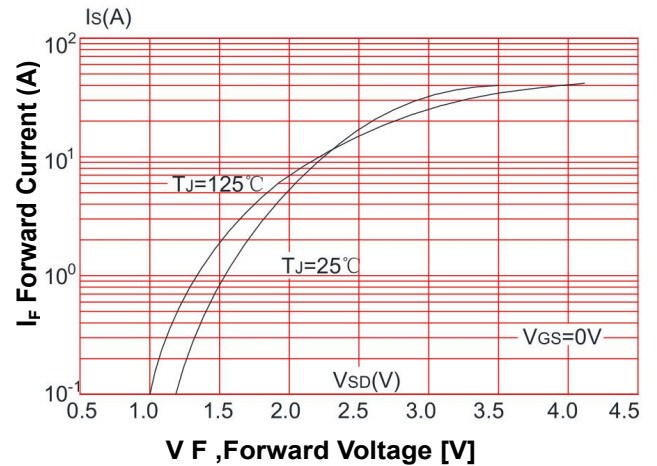


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

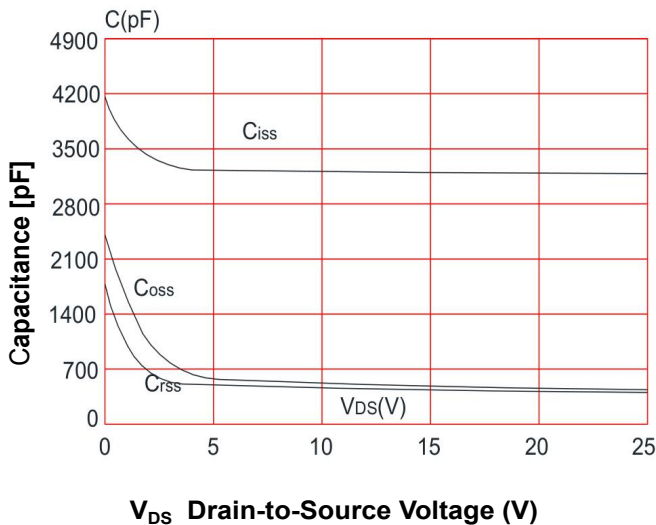


Figure 5. Capacitance Characteristics

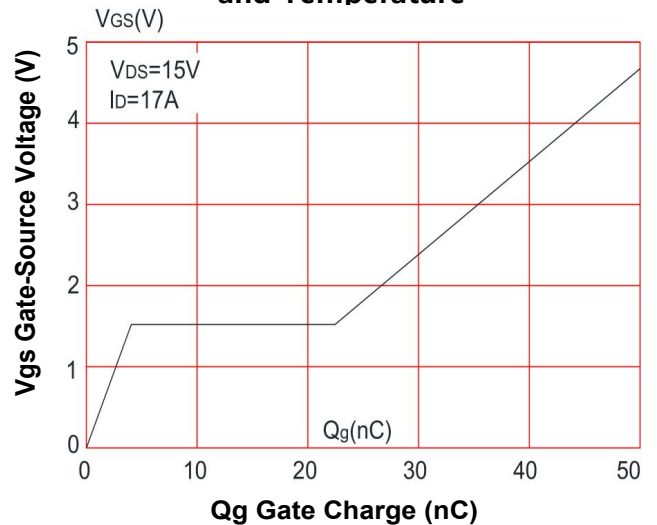
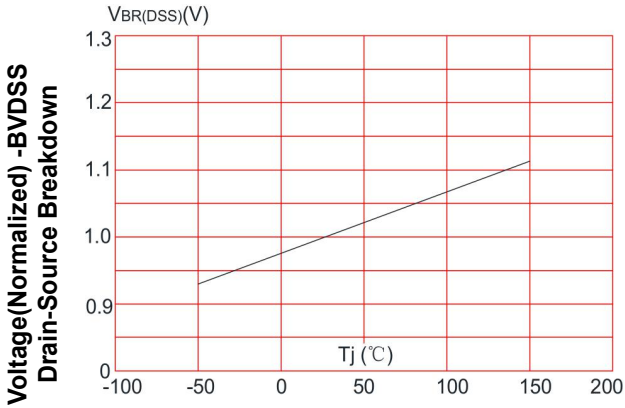
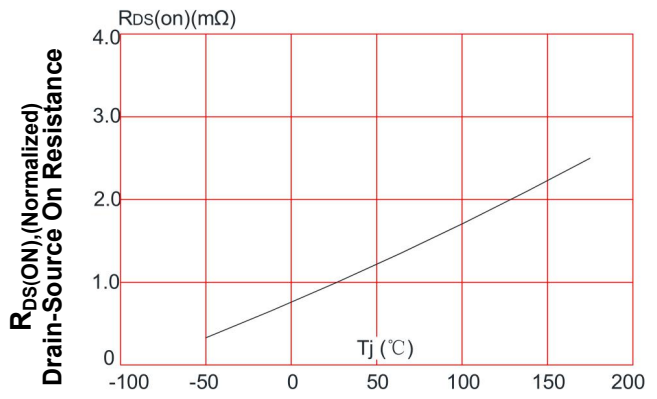


Figure 6. Gate Charge Characteristics

N- Channel Typical Characteristics (Continued)



T J , Junction Temperature [°C]
Figure 7. Breakdown Voltage Variation vs Temperature



T J , Junction Temperature [°C]
Figure 8. On-Resistance Variation vs Temperature

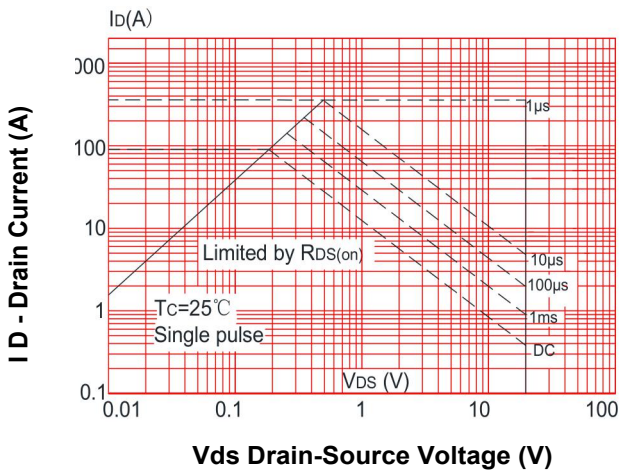
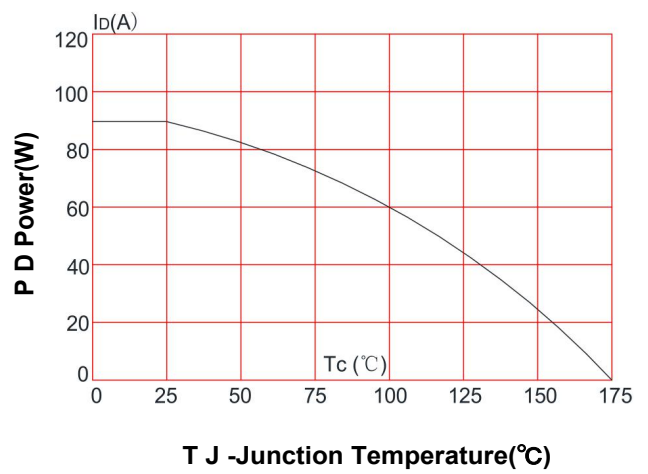


Figure 9. Maximum Safe Operating Area



T J -Junction Temperature(°C)
Figure 10. Maximum Power Dissipation vs Case Temperature

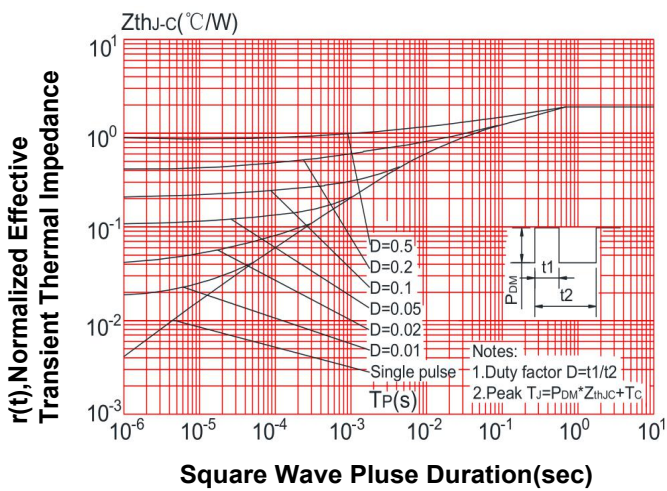
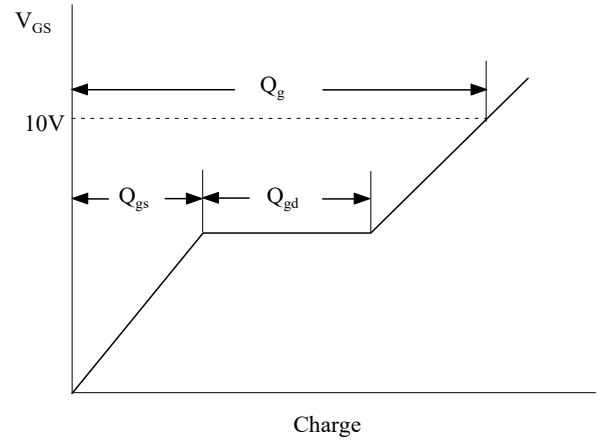
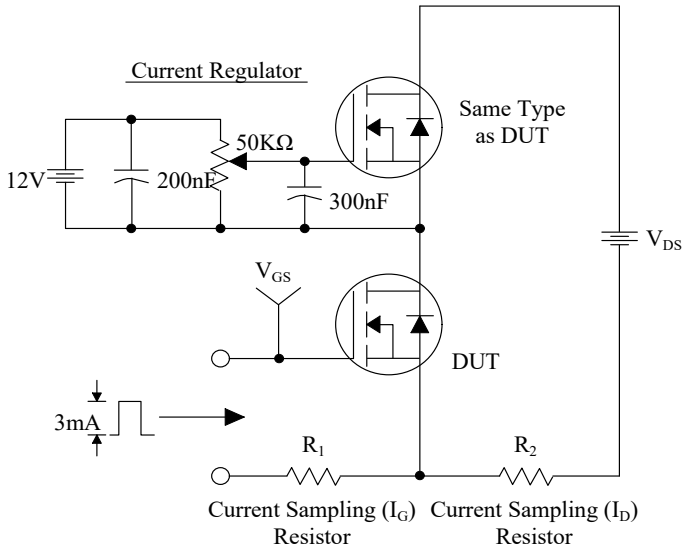
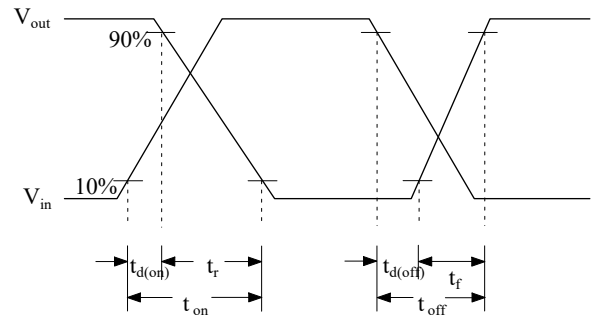
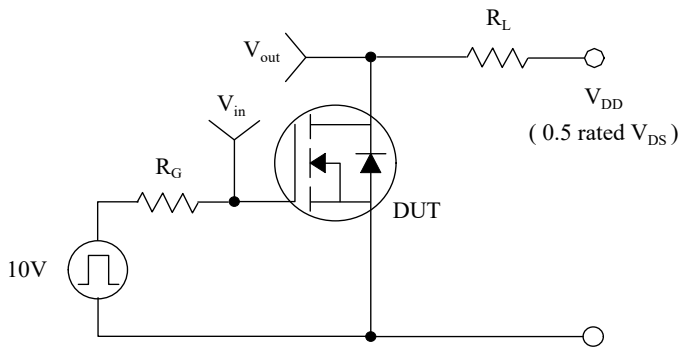


Figure 11. Transient Thermal Response Curve

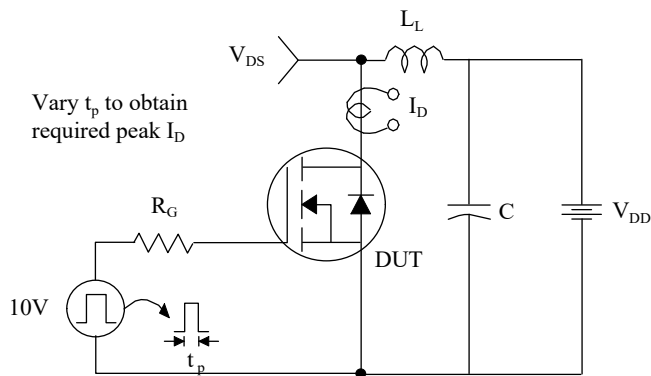
Gate Charge Test Circuit & Waveform



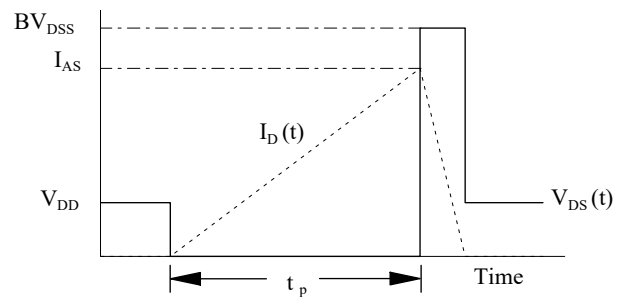
Resistive Switching Test Circuit & Waveforms



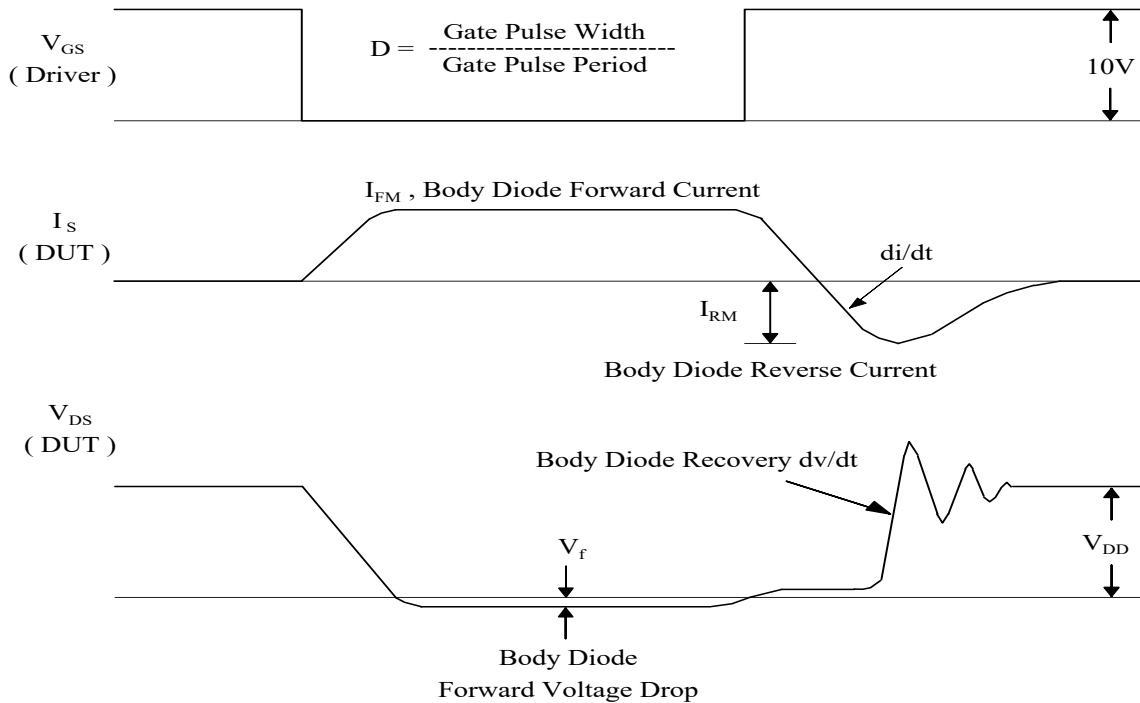
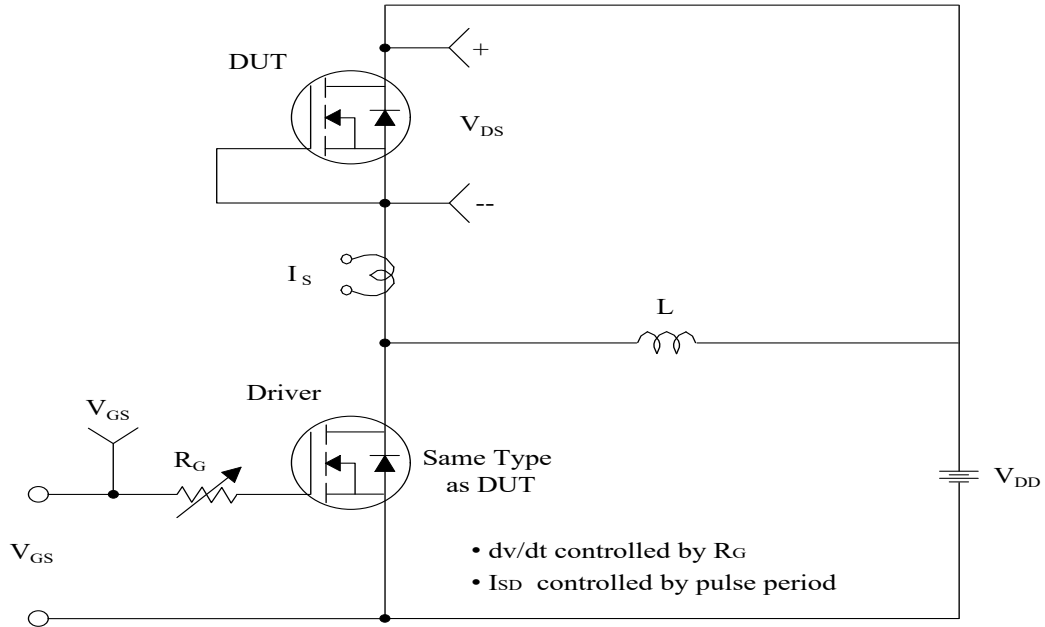
Unclamped Inductive Switching Test Circuit & Waveforms



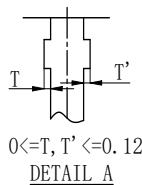
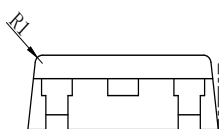
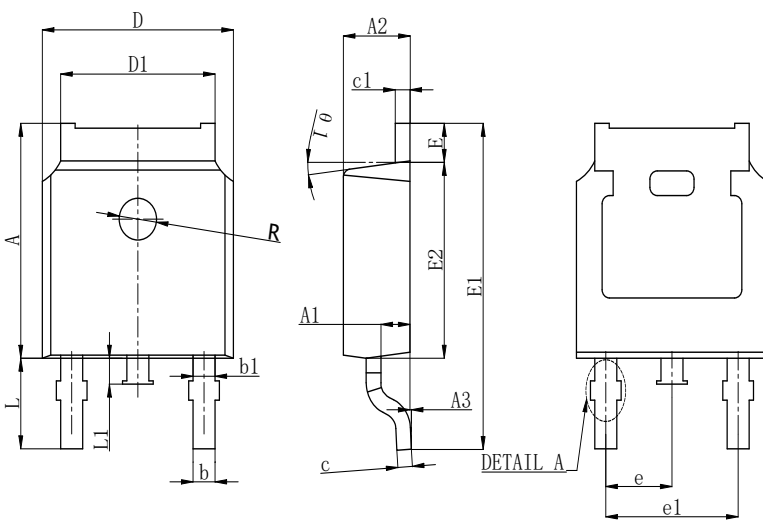
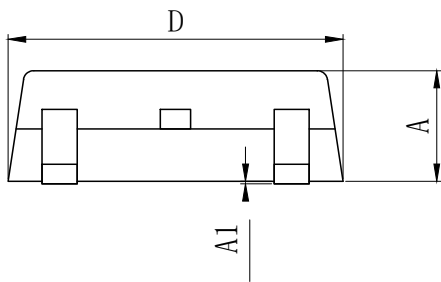
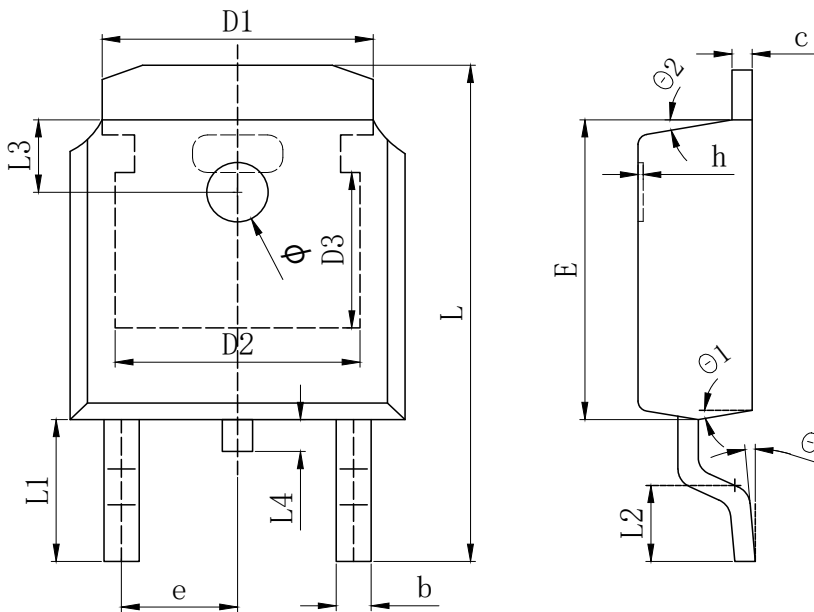
$$E_{AS} = \frac{1}{2} L_L I_{AS}^2$$



Peak Diode Recovery dv/dt Test Circuit & Waveforms



TO-252 Package Outline Data



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c (电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
φ	1.100	1.200	1.300
θ	0°		8°
θ 1	9° TYP		
θ 2	9° TYP		

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	7.050	7.100	7.150
A1	0.960	1.010	1.060
A2	2.250	2.300	2.350
A3	0.000	0.050	0.100
b	0.760REF.		
b1	1.000REF.		
c	0.508REF.		
c1	0.508REF.		
D	6.550	6.600	6.650
D1	5.220	5.320	5.420
E	0.950	1.000	1.050
E1	9.700	9.900	10.100
E2	6.050	6.100	6.150
e	2.286BSC		
e1	4.572REF.		
L	2.650	2.800	2.950
L1	0.700	0.800	0.900
θ 1	7° REF.		
R	1.300REF.		
R1	0.250REF.		


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